

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/634,917	08/06/2003	Wataru Saito	241189US2S 6489			
22850	7590 01/04/2005		EXAMINER			
•	PIVAK, MCCLELLAN	LEWIS, MONICA				
1940 DUKE ALEXANDI	RIA, VA 22314	ART UNIT	PAPER NUMBER			
		2822				
				DATE MAILED: 01/04/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application	on No.	Applicant(s)			
		10/634,91	7	SAITO ET AL.			
	Office Action Summary	Examiner		Art Unit			
		Monica L	ewis	2822			
Period fo	The MAILING DATE of this communication	appears on the	cover sheet with the	correspondence ac	ddress		
A SH THE - Exte after - If the - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR REMAILING DATE OF THIS COMMUNICATIOnsions of time may be available under the provisions of 37 CF SIX (6) MONTHS from the mailing date of this communication is period for reply specified above is less than thirty (30) days, by period for reply is specified above, the maximum statutory pure to reply within the set or extended period for reply will, by steply received by the Office later than three months after the red patent term adjustment. See 37 CFR 1.704(b).	ON R 1,136(a). In no even. a reply within the state eriod will apply and witatute, cause the app	ent, however, may a reply be ti utory minimum of thirty (30) da Il expire SIX (6) MONTHS fron ication to become ABANDON	mely filed ys will be considered time in the mailing date of this c ED (35 U.S.C. § 133).	ely. communication.		
Status							
1)⊠ 2a)□ 3)□	This action is FINAL . 2b) This action is non-final.						
Disposit	ion of Claims						
_	Claim(s) is/are rejected. Claim(s) is/are objected to.						
Applicat	ion Papers						
10)	The specification is objected to by the Example drawing(s) filed on is/are: a) Applicant may not request that any objection to Replacement drawing sheet(s) including the country The oath or declaration is objected to by the	accepted or b) the drawing(s) become clion is require	e held in abeyance. Seed if the drawing(s) is of	ee 37 CFR 1.85(a). ojected to. See 37 C			
Priority (under 35 U.S.C. § 119						
a)	Acknowledgment is made of a claim for for All b) Some * c) None of: 1. Certified copies of the priority docun 2. Certified copies of the priority docun 3. Copies of the certified copies of the application from the International Buse the attached detailed Office action for a	nents have bee nents have bee priority docume ireau (PCT Rul	n received. n received in Applica ents have been receiv e 17.2(a)).	tion No red in this National	l Stage		
Attachmen	t(s)						
1)	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SE or No(s)/Mail Date		4) Interview Summar Paper No(s)/Mail D 5) Notice of Informal 6) Other:	ate	O-152)		

Art Unit: 2822

DETAILED ACTION

1. This restriction is in response to the election filed October 8, 2004.

Election/Restrictions

2. This application contains claims directed to the following patentably distinct species of the claimed invention:

Embodiment I (Claims 1-4, 9-11 and 24), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode, wherein the field plate electrode is connected to the first main electrode and the third semiconductor layer is formed so as to cover the second main electrode;

Embodiment II (Claims 1-3, 14 and 24), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode, wherein the field plate electrode is connected to the first main electrode and a gate insulation film is formed under the control electrode; Embodiment III (Claims 1-3, 23 and 24), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the

Art Unit: 2822

second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode, wherein the field plate electrode is connected to the first main electrode and the three layers are formed of diamond; Embodiment IV (Claims 1, 12 and 13), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode, insulation film formed on the third layer and field plate electrode formed on the insulation film and connected to the first main electrode and the control electrode; Embodiment V (Claims 1 and 5-8), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main and a fifth semiconductor layer of the first conductivity type formed under the second main electrode; Embodiment VI (Claims 1, 15, 17, 19 and 21), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode and a heterojunction of AlGaN and GaN;

Art Unit: 2822

Embodiment VII (Claims 1, 16, 18, 20 and 22), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and second main electrode and a heterojunction of AlGaInN and GaInN;

Embodiment VIII (Claims 1 and 25), directed to a power semiconductor device having a first semiconductor layer, a second semiconductor layer, first and second main electrodes formed on the second layer separately from each other, control electrode and third semiconductor layer formed between the control and the first and third layers are formed of an intrinsic semiconductor.

Applicant is required under 35 U.S.C. 121 to elect a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable. Currently, none are generic.

Applicant is advised that a reply to this requirement must include an identification of the species that is elected consonant with this requirement, and a listing of all claims readable thereon, including any claims subsequently added. An argument that a claim is allowable or that all claims are generic is considered nonresponsive unless accompanied by an election.

Upon the allowance of a generic claim, applicant will be entitled to consideration of claims to additional species which are written in dependent form or otherwise include all the limitations of an allowed generic claim as provided by 37 CFR 1.141. If claims

Art Unit: 2822

are added after the election, applicant must indicate which are readable upon the elected species. MPEP § 809.02(a).

Should applicant traverse on the ground that the species are not patentably distinct, applicant should submit evidence or identify such evidence now of record showing the species to be obvious variants or clearly admit on the record that this is the case. In either instance, if the examiner finds one of the inventions unpatentable over the prior art, the evidence or admission may be used in a rejection under 35 U.S.C. 103(a) of the other invention.

3. Applicant is reminded that upon the cancellation of claims to a non-elected invention, the inventorship must be amended in compliance with 37 CFR 1.48(b) if one of the currently named inventors is no longer an inventor of at least one claim remaining in the application. Any amendment of inventorship must be accompanied by a request under 37 CFR 1.48(b) and by the fee under 37 CFR 1.17(i).

Conclusion

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica Lewis whose telephone number is 571-272-1838. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722 for regular and after final communications. Any inquiry of a general nature or relating to the

Art Unit: 2822

status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

ML

December 22, 2004

Mary Wilczewski Primary Examiner